

BUV21

SWITCHMODE™ Series NPN Silicon Power Transistor

This device is designed for high speed, high current, high power applications.

Features

- High DC Current Gain:
 $h_{FE} \min = 20$ at $I_C = 12$ A
- Low $V_{CE(sat)}$, $V_{CE(sat)}$
 $\max = 0.6$ V at $I_C = 8$ A
- Very Fast Switching Times:
 $T_F \max = 0.4$ μ s at $I_C = 25$ A
- These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO(SUS)}$	200	Vdc
Collector-Base Voltage	V_{CBO}	250	Vdc
Emitter-Base Voltage	V_{EBO}	7	Vdc
Collector-Emitter Voltage ($V_{BE} = -1.5$ V)	V_{CEX}	250	Vdc
Collector-Emitter Voltage ($R_{BE} = 100 \Omega$)	V_{CER}	240	Vdc
Collector-Current – Continuous	I_C	40	Adc
– Peak ($PW \leq 10$ ms)	I_{CM}	50	Apk
Base-Current Continuous	I_B	8	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$	P_D	250	W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to 200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θ_{JC}	0.7	$^\circ\text{C/W}$

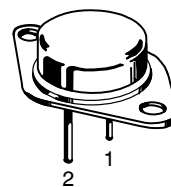
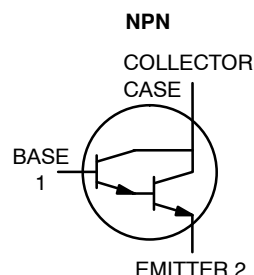
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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**40 AMPERES
NPN SILICON POWER
METAL TRANSISTOR
200 VOLTS – 250 WATTS**



TO-204AE (TO-3)
CASE 197A
STYLE 1

MARKING DIAGRAM



BUV21 = Device Code
G = Pb-Free Package
A = Assembly Location
Y = Year
WW = Work Week
MEX = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping
BUV21G	TO-204 (Pb-Free)	100 Units / Tray

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BUV21

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS (Note 1)

Collector-Emitter Sustaining Voltage ($I_C = 200\text{ mA}$, $I_B = 0$, $L = 25\text{ mH}$)	$V_{CE(sus)}$	200		Vdc
Collector Cutoff Current at Reverse Bias: ($V_{CE} = 250\text{ V}$, $V_{BE} = -1.5\text{ V}$) ($T_C = 25^\circ\text{C}$ unless otherwise noted) ($V_{CE} = 250\text{ V}$, $V_{BE} = -1.5\text{ V}$, $T_C = 125^\circ\text{C}$)	I_{CEX}		3.0 12.0	mAdc
Collector-Emitter Cutoff Current ($V_{CE} = 160\text{ V}$)	I_{CEO}		3.0	mAdc
Emitter-Base Reverse Voltage ($I_E = 50\text{ mA}$)	V_{EBO}	7		V
Emitter-Cutoff Current ($V_{EB} = 5\text{ V}$)	I_{EBO}		1.0	mAdc

SECOND BREAKDOWN

Second Breakdown Collector Current with base forward biased ($V_{CE} = 20\text{ V}$, $t = 1\text{ s}$) ($V_{CE} = 140\text{ V}$, $t = 1\text{ s}$)	$I_{S/b}$	12 0.15		Adc
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ON CHARACTERISTICS (Note 1)

DC Current Gain ($I_C = 12\text{ A}$, $V_{CE} = 2\text{ V}$) ($I_C = 25\text{ A}$, $V_{CE} = 4\text{ V}$)	h_{FE}	20 10	60	
Collector-Emitter Saturation Voltage ($I_C = 12\text{ A}$, $I_B = 1.2\text{ A}$) ($I_C = 25\text{ A}$, $I_B = 3\text{ A}$)	$V_{CE(sat)}$		0.6 1.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 25\text{ A}$, $I_B = 3\text{ A}$)	$V_{BE(sat)}$		1.5	Vdc

DYNAMIC CHARACTERISTICS

Current Gain – Bandwidth Product ($V_{CE} = 15\text{ V}$, $I_C = 2\text{ A}$, $f = 4\text{ MHz}$)	f_T	8.0		MHz
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SWITCHING CHARACTERISTICS (Resistive Load)

Turn-on Time	($I_C = 25\text{ A}$, $I_{B1} = I_{B2} = 3\text{ A}$, $V_{CC} = 100\text{ V}$, $R_C = 4\ \Omega$)	t_{on}	1.0	μs
Storage Time		t_s	1.8	
Fall Time		t_f	0.4	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

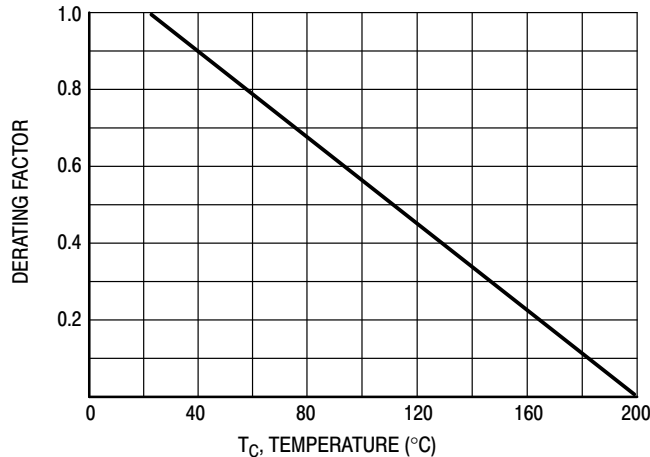


Figure 1. Power Derating

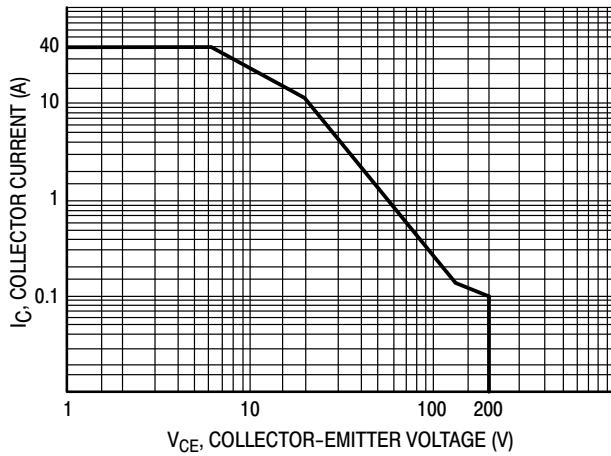


Figure 2. Active Region Safe Operating Area

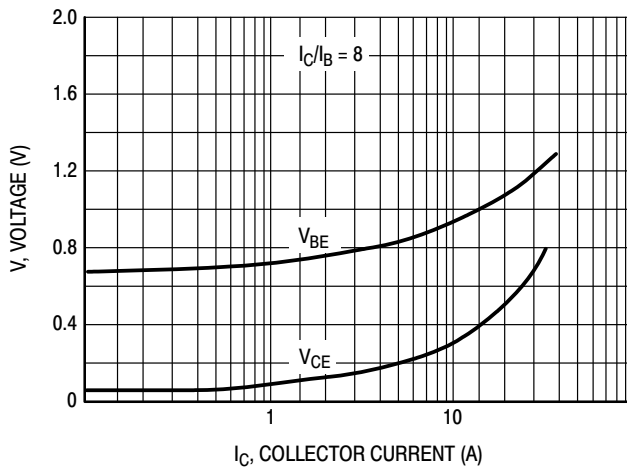


Figure 3. "On" Voltages

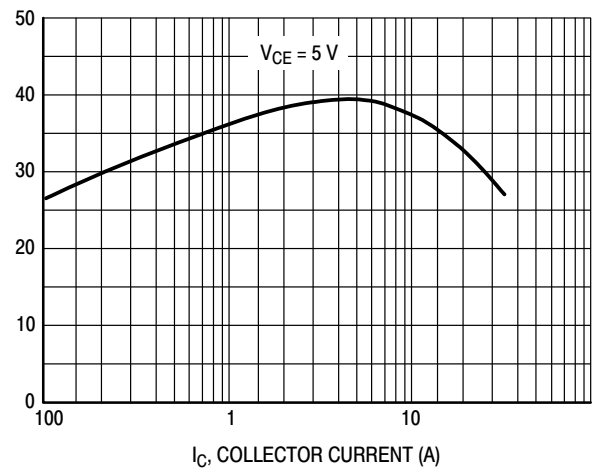


Figure 4. DC Current Gain

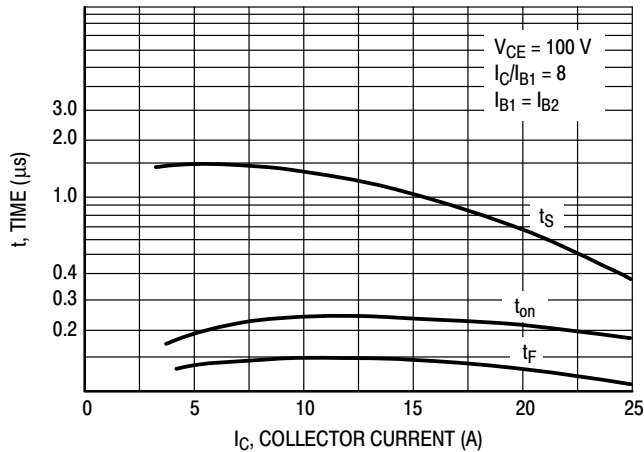


Figure 5. Resistive Switching Performance

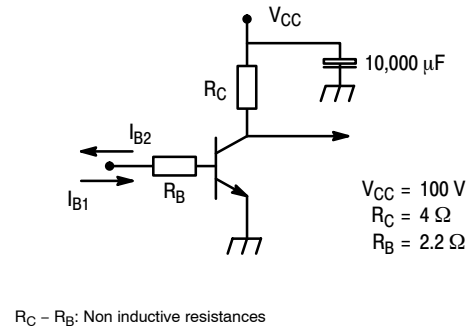
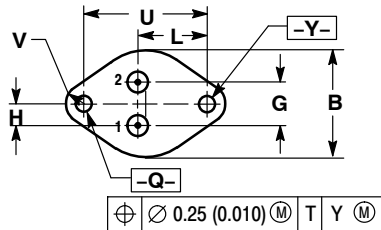
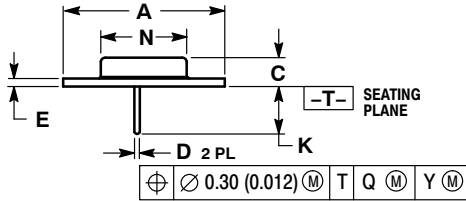


Figure 6. Switching Times Test Circuit

BUV21

PACKAGE DIMENSIONS

TO-204 (TO-3)
CASE 197A-05
ISSUE K



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.530 REF	38.86 REF		
B	0.990	1.050	25.15	26.67
C	0.250	0.335	6.35	8.51
D	0.057	0.063	1.45	1.60
E	0.060	0.070	1.53	1.77
G	0.430 BSC	10.92 BSC		
H	0.215 BSC	5.46 BSC		
K	0.440	0.480	11.18	12.19
L	0.665 BSC	16.89 BSC		
N	0.760	0.830	19.31	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC	30.15 BSC		
V	0.131	0.188	3.33	4.77

STYLE 1:

- PIN 1: BASE
2: EMITTER
CASE: COLLECTOR

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